



HGP098N10S

Electrical Characteristics at  $T_J=25^\circ\text{C}$  (unless otherwise specified)

## Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\text{ A}$	100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\text{ A}$	2.0	3.0	4.0	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS}=0V, V_{DS}=100V, T_J=25^\circ\text{C}$	-	-	1	A
		$V_{GS}=0V, V_{DS}=100V, T_J=100^\circ\text{C}$	-	-	100	
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	9	10.2	m
Transconductance	$g_{fs}$	$V_{DS}=5V, I_D=20A$	-	45	-	S
Gate Resistance	$R_G$	$V_{GS}=0V, V_{DS}\text{ Open}, f=1\text{MHz}$	-	2.4	-	

## Dynamic Characteristics

Input Capacitance	$C_{iss}$		-	1571	-	pF
Output Capacitance	$C_{oss}$	$V_{GS}=0V, V_{DS}=50V, f=1\text{MHz}$	-	468	-	
Reverse Transfer Capacitance	$C_{rss}$		-	9.7	-	
Total Gate Charge	$Q_g(10V)$		-	20	-	nC
Gate to Source Charge	$Q_{gs}$	$V_{DD}=50V, I_D=20A, V_{GS}=10V$	-	6.4	-	
Gate to Drain (Miller) Charge	$Q_{gd}$		-	3.6	-	
Turn on Delay Time	$t_{d(on)}$		-	14	-	
Rise time	$t_r$	$V_{DD}=50V, I_D=20A, V_{GS}=10V,$	-	5	-	
Turn off Delay Time	$t_{d(off)}$	$R_G=10\ \Omega$	-	20	-	
Fall Time	$t_f$		-	5	-	

## Reverse Diode Characteristics

Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_F=20A$	-	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$V_R=50V, I_F=20A, di_F/dt=500A/\text{s}$	-	36	-	ns
Reverse Recovery Charge	$Q_{rr}$		-	131	-	nC

Fig 1. Typical Output Characteristics

Figure 2. On-Resistance vs. Gate-Source Voltage

Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

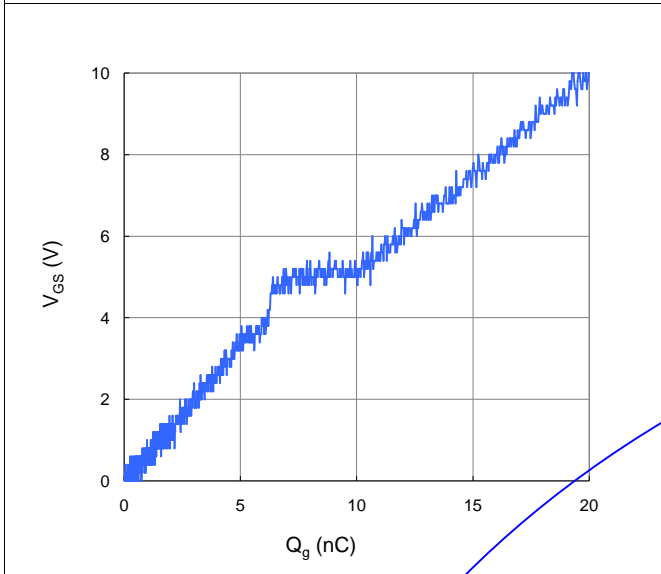


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

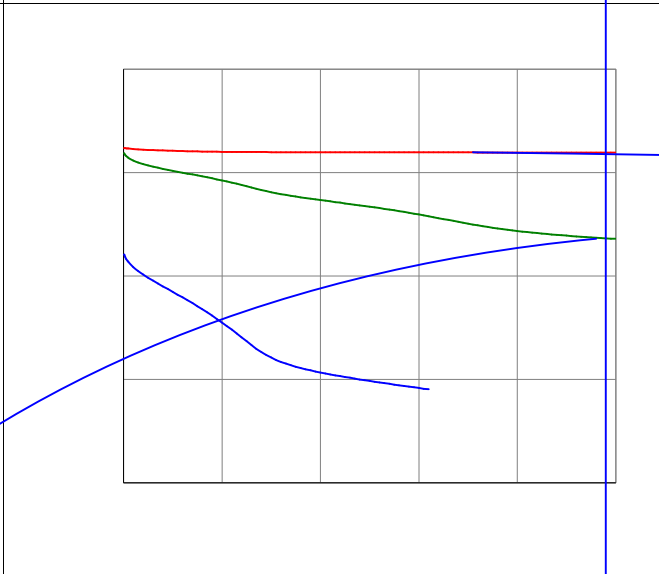


Figure 9. Maximum Safe Operating Area

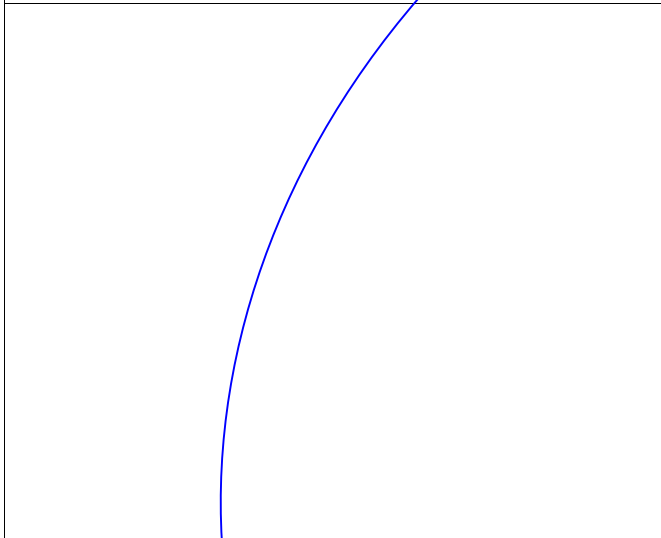


Figure 10. Maximum Drain Current vs. Case Temperature

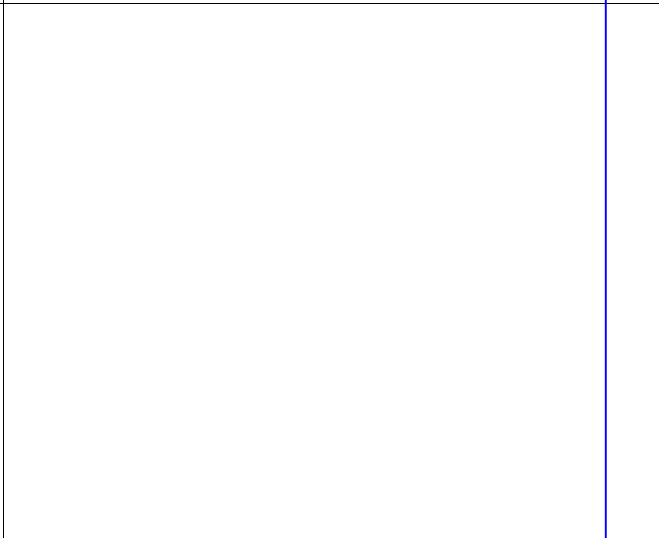
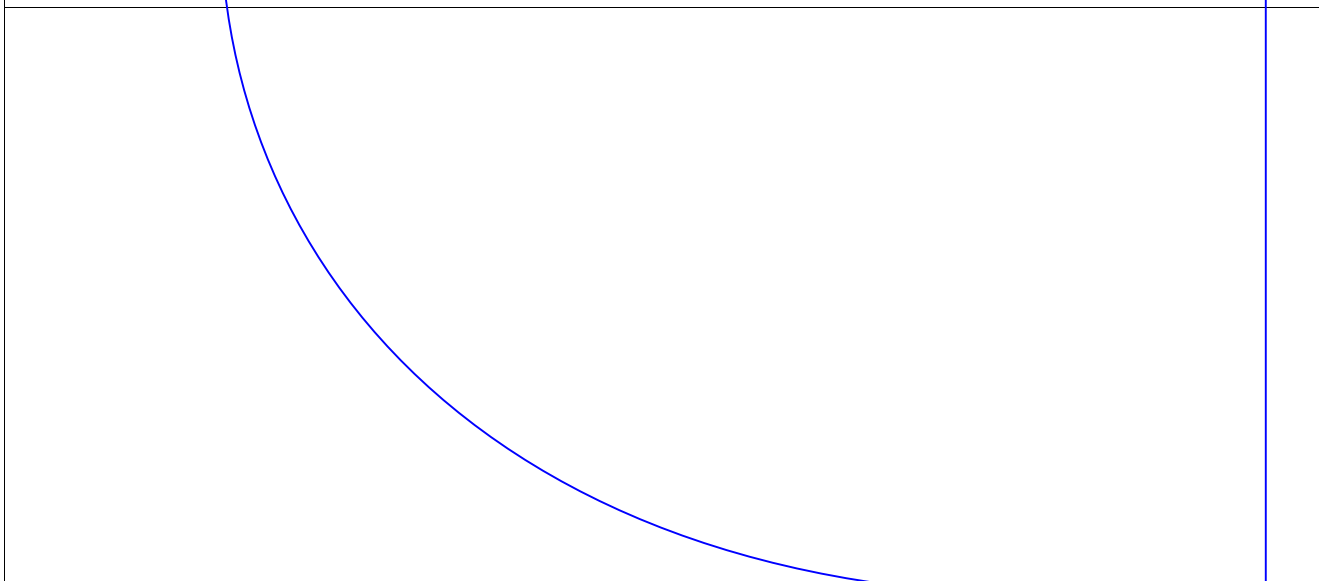
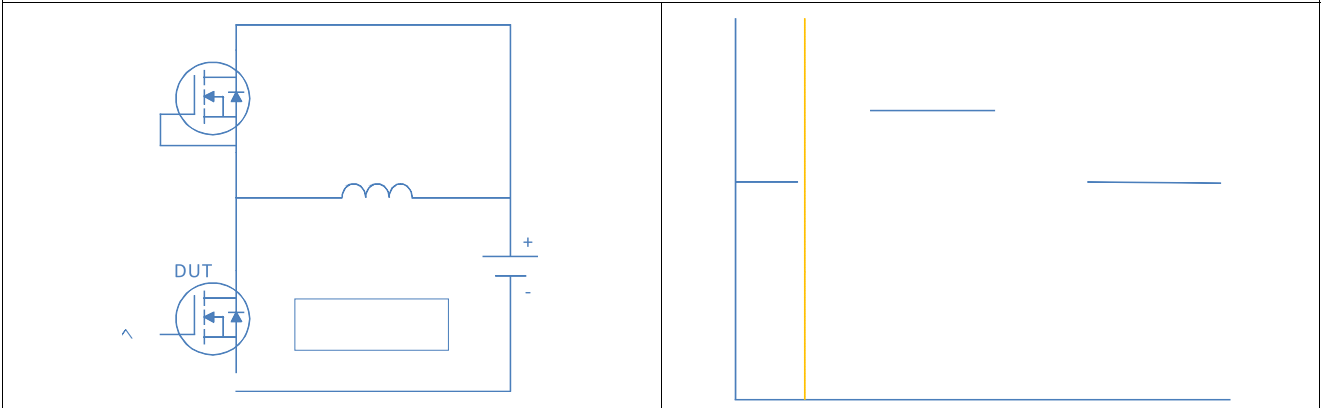


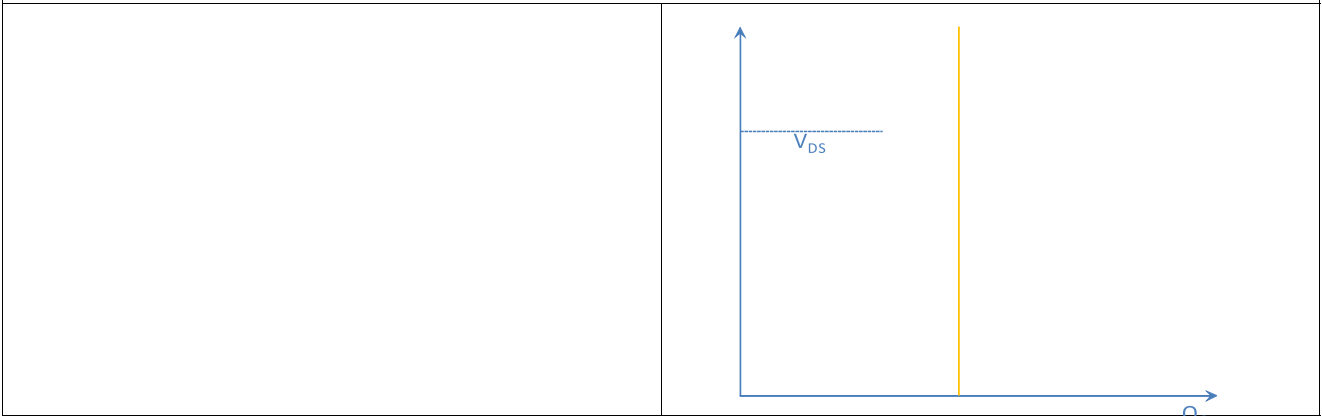
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient



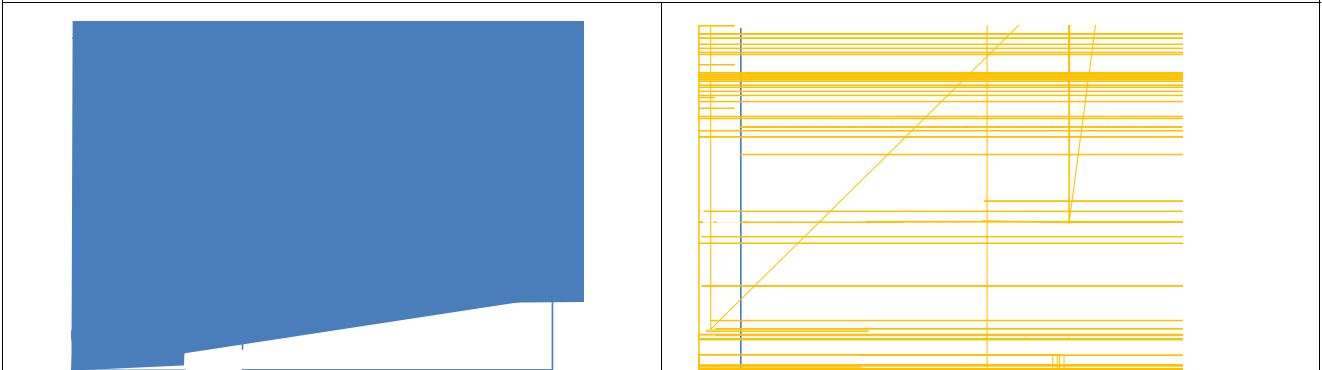
Inductive switching Test



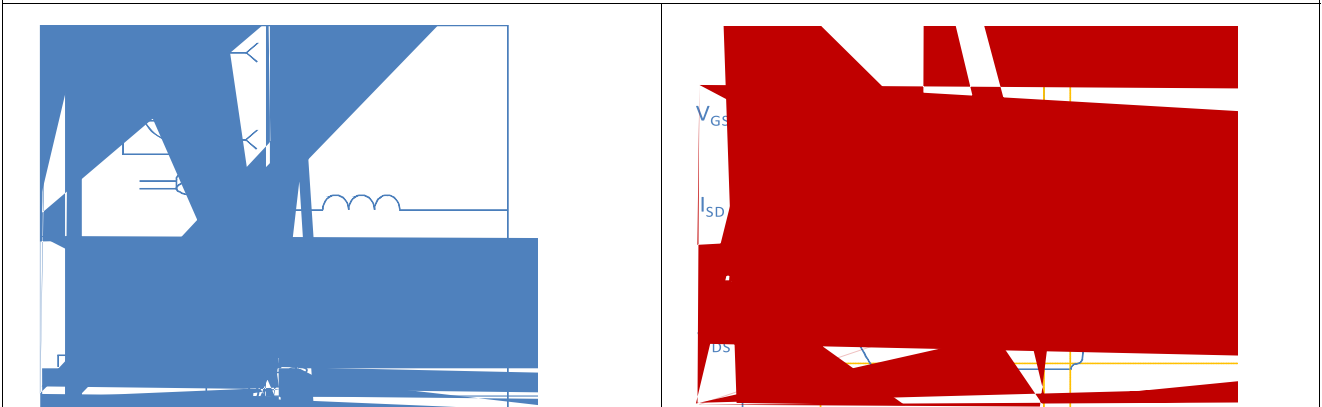
Gate Charge Test



Uclamped Inductive Switching (UIS) Test

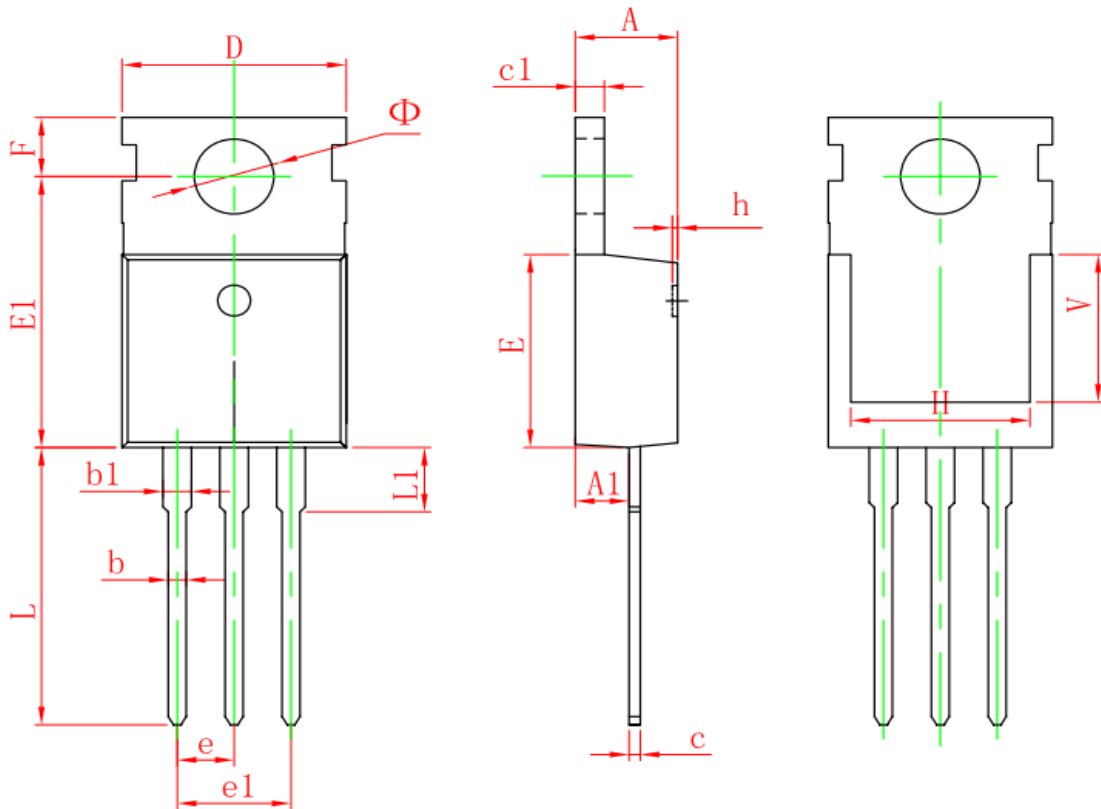


Diode Recovery Test



Package Outline

TO-220, 3 leads



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
h	0.300	0.000	0.012	0.000
L	13.400	0.508	0.528	12.900
L1	3.250	0.112	0.128	2.850
V	6.900 R=	0.276 R=		
Φ	3.800	0.134	0.150	3.400